C3P5 Improved CPV Technology with Fifth Generation Wafer Processing

- **Enhanced efficiency and lower cost with the demonstrated reliability of our C3MJ technology**
- **Fully qualified and production-ready**
- **Grid design optimized for high concentration (1200x)**

**Product Description**
- Typical Efficiency: 39.5%
- Recommended operating temperature: <110°C

**Epitaxial Structure**
- Triple junction solar cell on Germanium substrate
  - GaInP (1.88 eV) / GaInAs (1.41 eV) / Ge (0.67 eV)

**Metallization**
- Silver metallization on front busbar and grid fingers.
- Gold flash front contact finish is available as a special order with minimum lot sizes imposed.
- Silver metallization with 500Å gold on back surface

**Mechanical Dimensions**

**CPV Cell Ordering Guide**

**Packaging Format**
- PP – 046556 – CCC

**Configuration Options**
- 11 – Processed Wafer
- 21 – Bare Cell in Waffle Tray
- 351 – Silver front contact finish

Example:
- 21-046556-351 Bare Cell in Waffle Tray, Silver Front Contact

Specifications Subject to Change without Notice.